

## ABSTRACT

A light-emitting apparatus employing a GaN-based semiconductor. The light-emitting apparatus comprises an n-type clad layer (124); an active layer (129) including an n-type first barrier layer (126), well layers (128), and second barrier layers (130); a p-type block layer (132); and a p-type clad layer (134). By setting the band gap energy  $E_{gb}$  of the p-type block layer (132), the band gap energy  $E_{g2}$  of the second barrier layers (130), the band gap energy  $E_{g1}$  of the first barrier layer (126), and the band gap energy  $E_{gc}$  of the n-type and the p-type clad layers such that the relationship  $E_{gb} > E_{g2} > E_{g1} \geq E_{gc}$  is satisfied; the carriers can be efficiently confined; and the intensity of the light emission can be increased.